PHU78NQ03LT

N-channel TrenchMOS logic level FET

Rev. 06 — 15 June 2009 Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Suitable for high frequency applications due to fast switching characteristics
- Suitable for logic level gate drive sources

1.3 Applications

- Computer motherboards
- DC-to-DC convertors

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	-	25	V
I_D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1; see Figure 3	-	-	75	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	-	107	W
Dynamic characteristics						
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12 V; T_j = 25 °C; see Figure 9; see Figure 10	-	4	-	nC
Static characteristics						
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 7; see Figure 8	-	7.65	9	mΩ

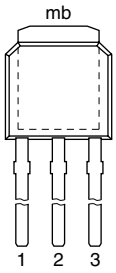
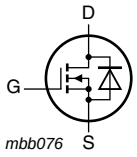
2. Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
PHU78NQ03LT	IPAK	plastic single-ended package (IPAK); 3 leads (in-line)	SOT533

3. Pinning information

Table 3. Pinning information

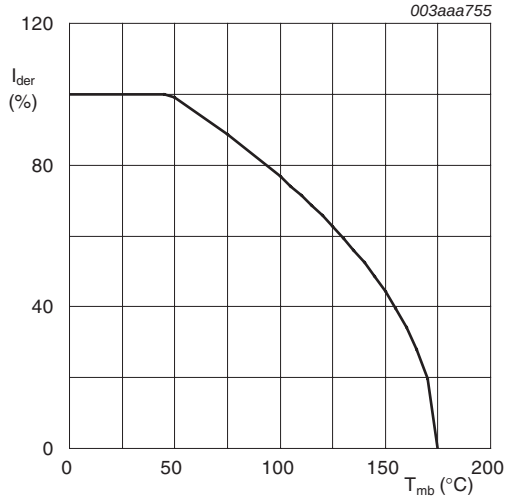
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 SOT533 (IPAK)	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

4. Limiting values

Table 4. Limiting values

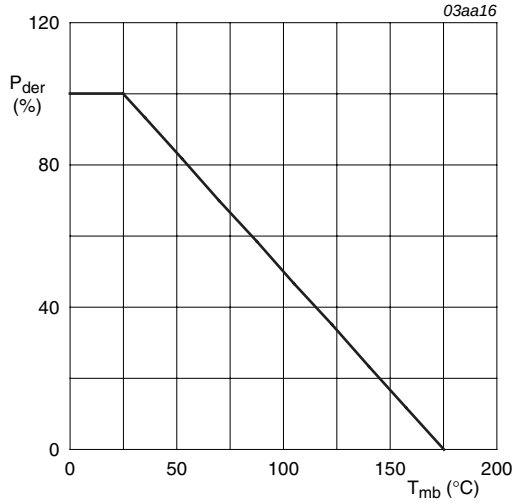
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C	-	25	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 kΩ; $T_{mb} \geq 25$ °C; $T_{mb} \leq 175$ °C	-	25	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	V_{GS} = 5 V; T_{mb} = 100 °C	-	46.9	A
		V_{GS} = 10 V; T_{mb} = 100 °C; see Figure 1	-	57.5	A
		V_{GS} = 10 V; T_{mb} = 25 °C; see Figure 1; see Figure 3	-	75	A
		V_{GS} = 5 V; T_{mb} = 25 °C	-	66.4	A
I_{DM}	peak drain current	$t_p \leq 10$ µs; pulsed; T_{mb} = 25 °C; see Figure 3	-	240	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; see Figure 2	-	107	W
T_{stg}	storage temperature		-55	175	°C
T_j	junction temperature		-55	175	°C
Source-drain diode					
I_S	source current	T_{mb} = 25 °C	-	75	A
I_{SM}	peak source current	$t_p \leq 10$ µs; pulsed; T_{mb} = 25 °C	-	240	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 32 A; $V_{sup} \leq 25$ V; unclamped; t_p = 0.17 ms; R_{GS} = 50 Ω	-	100	mJ



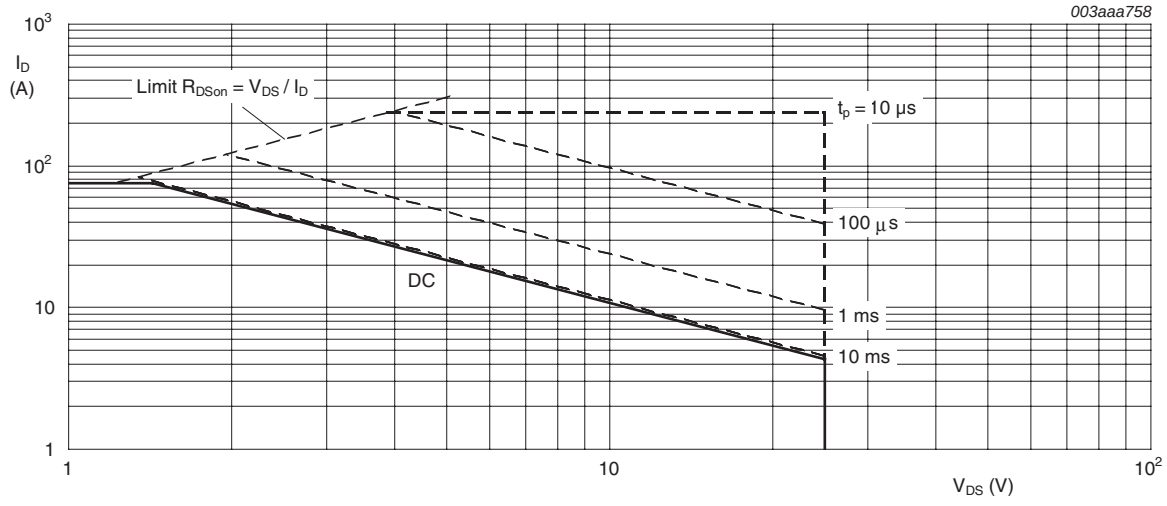
$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\,\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25°C; I_{DM}$ is single pulse; $V_{GS} = 10V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.4	K/W
$R_{th(j\text{-}a)}$	thermal resistance from junction to ambient	vertical in free air	-	70	-	K/W

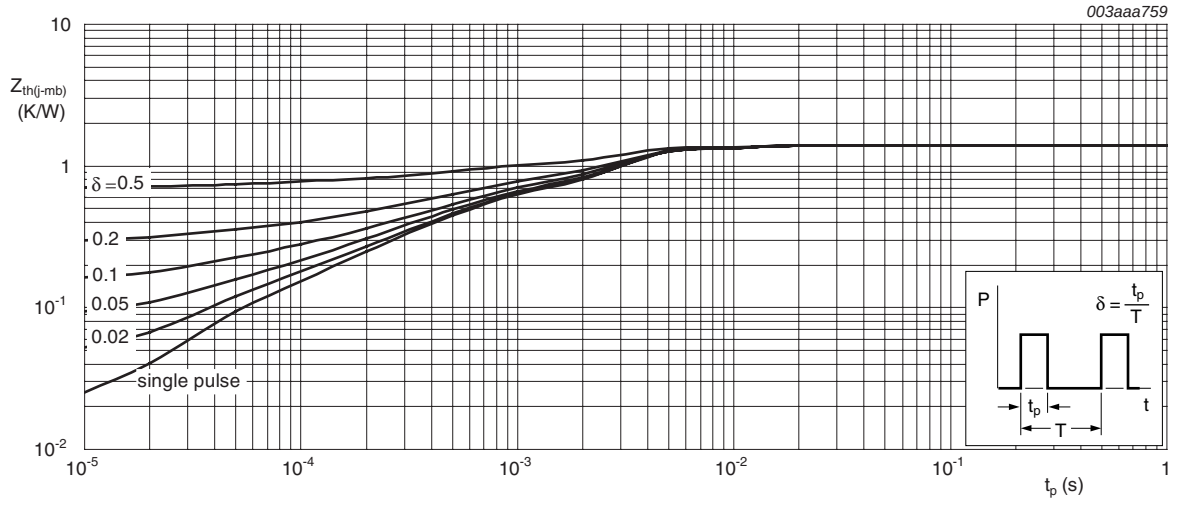


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

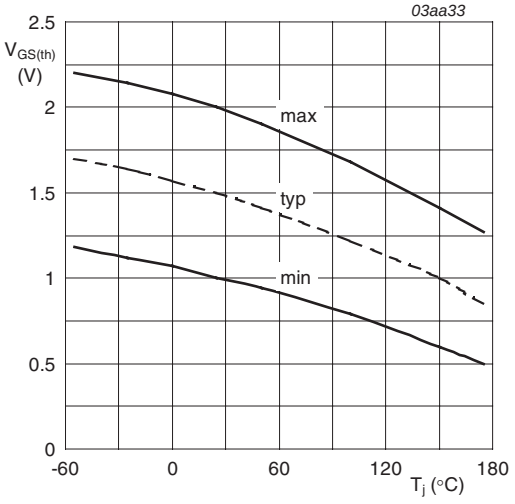
6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	22	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	25	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; see Figure 5; see Figure 6	-	-	2.2	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; see Figure 5; see Figure 6	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; see Figure 5; see Figure 6	1	1.5	2	V
I_{DSS}	drain leakage current	V_{DS} = 25 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	µA
		V_{DS} = 25 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	µA
I_{GSS}	gate leakage current	V_{GS} = 15 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -15 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 7; see Figure 8	-	7.65	9	mΩ
		V_{GS} = 5 V; I_D = 25 A; T_j = 175 °C; see Figure 7; see Figure 8	-	18.9	24.3	mΩ
		V_{GS} = 5 V; I_D = 25 A; T_j = 25 °C; see Figure 7; see Figure 8	-	10.5	13.5	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz; T_j = 25 °C	-	1	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	I_D = 0 A; V_{DS} = 0 V; V_{GS} = 4.5 V; T_j = 25 °C	-	8.6	-	nC
		I_D = 25 A; V_{DS} = 12 V; V_{GS} = 4.5 V; T_j = 25 °C; see Figure 9; see Figure 10	-	11	-	nC
Q_{GS}	gate-source charge	I_D = 25 A; V_{DS} = 12 V; V_{GS} = 4.5 V; T_j = 25 °C; see Figure 10; see Figure 10	-	3.6	-	nC
Q_{GS1}	pre-threshold gate-source charge		-	1.8	-	nC
Q_{GS2}	post-threshold gate-source charge		-	1.8	-	nC
Q_{GD}	gate-drain charge		-	4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I_D = 25 A; V_{DS} = 12 V; T_j = 25 °C; see Figure 9; see Figure 10	-	3	-	V
C_{iss}	input capacitance	V_{DS} = 12 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 11	-	970	-	pF
			-	1460	-	pF
C_{oss}	output capacitance		-	415	-	pF
C_{rss}	reverse transfer capacitance		-	170	-	pF

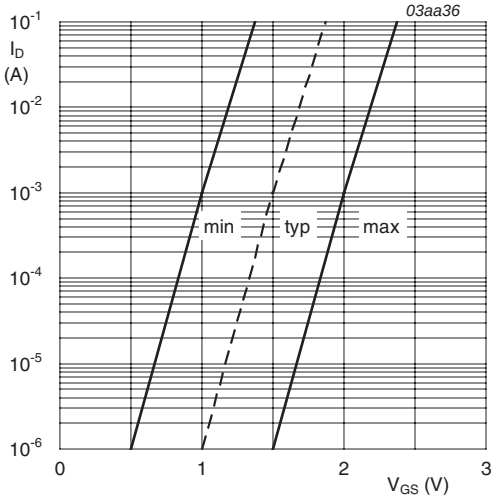
Table 6. Characteristics *...continued*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	V_{DS} = 12 V; R_L = 0.5 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 5.6 Ω; T_j = 25 °C	-	13	-	ns
t_r	rise time		-	46	-	ns
$t_{d(off)}$	turn-off delay time		-	20	-	ns
t_f	fall time		-	15	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; see Figure 12	-	0.78	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C	-	35	-	ns
Q_r	recovered charge		-	20	-	nC



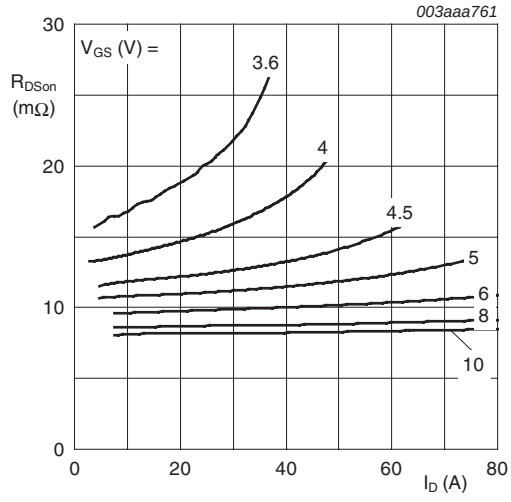
$I_D = 1\,mA; V_{DS} = V_{GS}$

Fig 5. Gate-source threshold voltage as a function of junction temperature



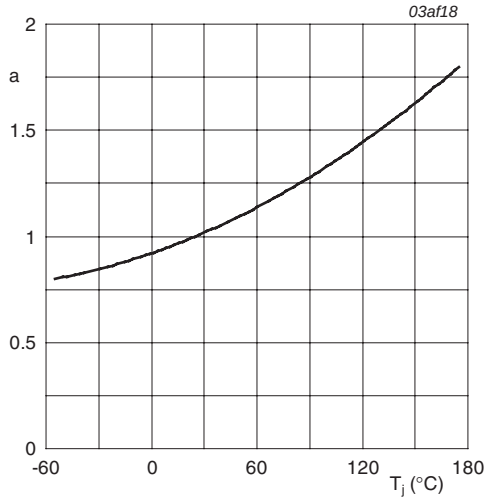
$T_j = 25\,°C; V_{DS} = V_{GS}$

Fig 6. Sub-threshold drain current as a function of gate-source voltage



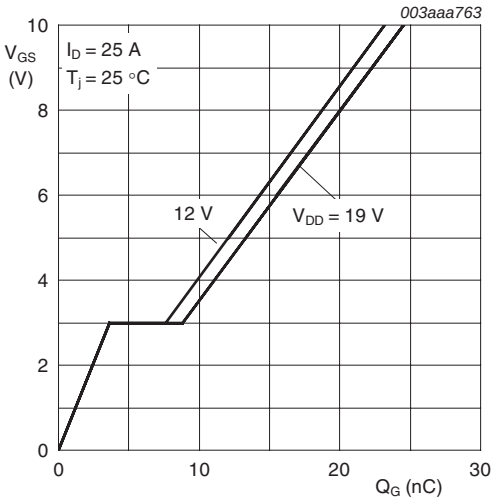
$T_j = 25°C$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25°C)}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



$I_D = 25A; V_{Ds} = 12V \text{ and } 19V$

Fig 9. Gate-source voltage as a function of gate charge; typical values

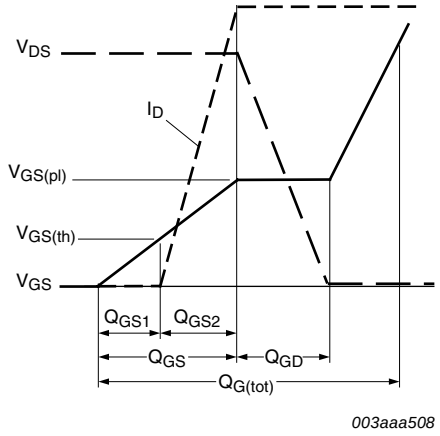
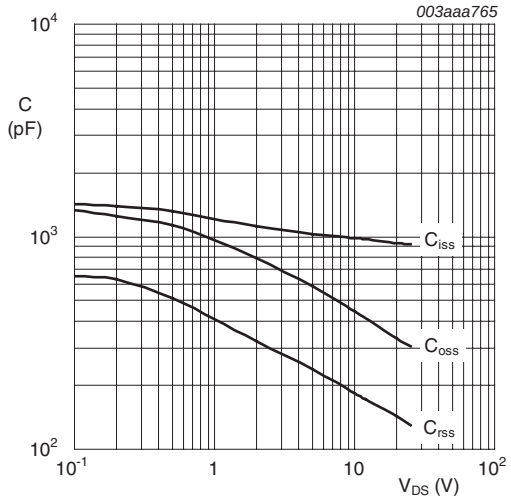
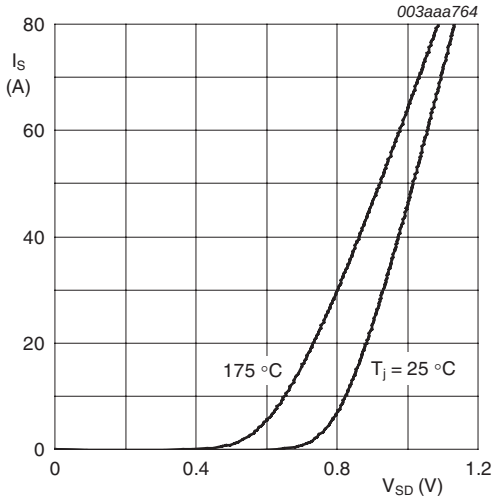


Fig 10. Gate charge waveform definitions



$V_{GS} = 0V; f = 1MHz$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

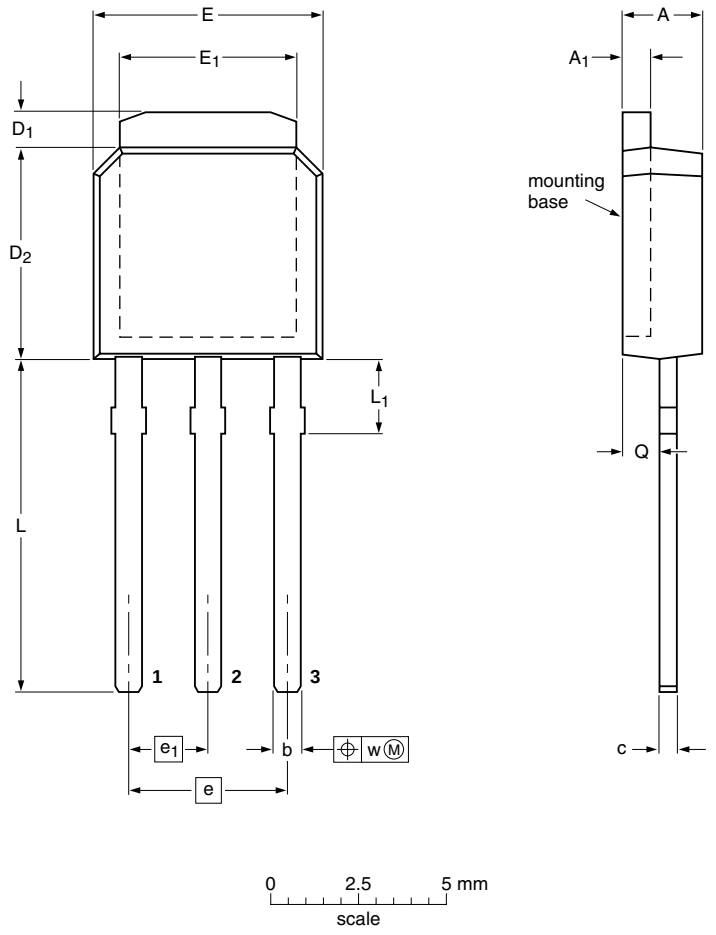


$T_j = 25°C \text{ and } 175°C; V_{GS} = 0V$

Fig 12. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package (IPAK); 3 leads (in-line) **SOT533**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	c	D_1	D_2	E	E_1	e	e_1	L	L_1 (2) max	Q	w
mm	2.38 2.22	0.93 0.46	0.89 0.71	0.56 0.46	1.10 0.96	6.22 5.98	6.73 6.47	5.21 5.00	4.57 BSC (1)	2.285 BSC (1)	9.6 9.2	2.7	1.1 1.0	0.3

Notes

1. Basic spacing between centers.
2. Terminal dimensions are uncontrolled within zone L_1.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT533		TO-251				~~05-02-11~~ 06-02-14

Fig 13. Package outline SOT533 (IPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHU78NQ03LT_6	20090615	Product data sheet	-	PHU_PHD78NQ03LT_5
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Type number PHU78NQ03LT separated from data sheet PHU_PHD78NQ03LT_5.			
PHU_PHD78NQ03LT_5 (9397 750 15084)	20050727	Product data sheet	-	PHP_PHU78NQ03LT_4
PHP_PHU78NQ03LT_4 (9397 750 13431)	20040726	Product data sheet	-	PHP_PHB_PHD78NQ03LT-03
PHP_PHB_PHD78NQ03LT-03 (9397 750 09667)	20020626	Product data	-	PHP_PHB_PHD78NQ03LT-02
PHP_PHB_PHD78NQ03LT-02 (9397 750 09418)	20020322	Product data	-	PHP_PHB_PHD78NQ03LT-01
PHP_PHB_PHD78NQ03LT-01 (9397 750 08916)	20011114	Product data	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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10. Contact information

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For sales office addresses, please send an email to: salesaddresses@nxp.com

11. Contents

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